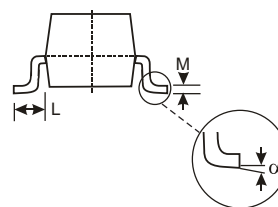
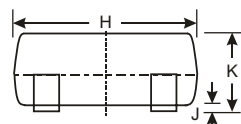
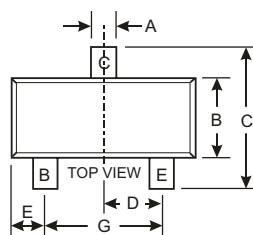
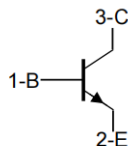
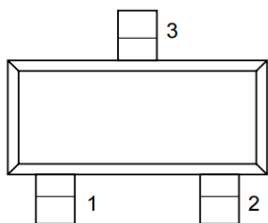


Features

- Complimentary to S8550
- Collector Current: $I_C=0.5A$
- Marking Code: J3Y



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current — Continuous	I_C	500	mA
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	417	$^\circ\text{C}/\text{W}$
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20\text{V}, I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE} = 1\text{V}, I_C = 50\text{mA}$	120		400	
	h_{FE2}	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_C = 20\text{mA}, f = 30\text{MHz}$	150			MHz

CLASSIFICATION OF h_{FE1}

Rank	L	H	J
Range	120-200	200-350	300-400

TYPICAL CHARACTERISTICS

